

# Emerging Memories

H.-S. Philip Wong

Center for Integrated Systems and Department of Electrical Engineering  
Stanford University, Stanford, California 94305

E-mail: [hspwong@stanford.edu](mailto:hspwong@stanford.edu)

Conventional memories such as SRAM, DRAM, and FLASH have set a very high cost/performance standard. Yet, recent advances in new materials, device technologies and circuits have made many emerging memories attractive candidates for a new generation of memories. This new generation of memories promise better or a different set of read, write, endurance, and retention characteristics from the conventional memories. It is also possible to contemplate new system design scenarios based on these new memory characteristics. In addition, the technology for integrating these new memories may permit three-dimensional stacking, integration of memory with CMOS logic on the same chip, or introduction of memory in new application areas such as flexible or large area electronics.

In this talk, we will give an overview of the various emerging memories followed by a discussion on possible applications.